

1. General description

WSJM65R044DW is a high voltage N-channel MOSFET in TO247 package, which utilizes the advanced super-junction technology to provide superior FOM $R_{DS(on)} * Q_g$ among silicon based MOSFETs. It is particularly suitable for applications require extreme high efficiency and power density.



2. Features and benefits

- Superior FOM $R_{DS(on)} * Q_g$
- Extremely low switching loss
- Integrated ultrafast body diode
- 100% avalanche tested

3. Applications

- EV charger
- High efficiency power supplies
- On board charger
- Inverters

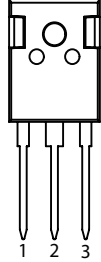
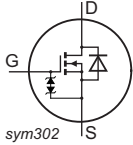
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute maximum rating							
V_{DS}	drain-source voltage			650			V
V_{GS}	gate-source voltage			±30			V
I_D	continuous drain current	$T_{mb} = 25\text{ °C}$		67			A
P_{tot}	power dissipation	$T_{mb} = 25\text{ °C}$		480			W
T_j	junction temperature			-55 to 150			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}, I_D = 34\text{ A}$		-	36	44	mΩ
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	$I_D = 34\text{ A}; V_{DS} = 400\text{ V}; V_{GS} = 10\text{ V}$		-	123	-	nC
E_{OSS}	COSS stored energy	$V_{GS} = 0\text{ V}; V_{DS} = 0\text{ to }400\text{ V}$		-	14.5	-	μJ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WSJM65R044DW	TO247	WSJM65R044DWQ	Tube	30	TO247N	20-July-2016

7. Marking

Table 4. Marking codes

Type number	Marking codes
WSJM65R044DW	WSJM 65R044DW

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{DS}	drain-source voltage			650	V
V_{GS}	gate-source voltage			± 30	V
I_D	continuous drain current	$T_{mb} = 25\text{ }^\circ\text{C}$		67	A
		$T_{mb} = 100\text{ }^\circ\text{C}$		42	A
I_{DM}	pulsed drain current	$T_{mb} = 25\text{ }^\circ\text{C}$		268	A
P_{tot}	power dissipation	$T_{mb} = 25\text{ }^\circ\text{C}$		480	W
E_{AS}	single pulse drain-to-source avalanche	$I_{AS} = 7.6\text{ A}$; $R_{GS} = 25\text{ }\Omega$; $V_{DD} = 50\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$		288	mJ
E_{AR}	repetitive avalanche energy	$I_{AS} = 7.6\text{ A}$; $R_{GS} = 25\text{ }\Omega$; $V_{DD} = 50\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$		1.01	mJ
I_{AS}	avalanche current, single pulse			7.6	A
dv/dt	MOSFET dv/dt ruggedness			72	V/ns
dv/dt	reverse diode dv/dt			50	V/ns
dI _r /dt	maximum diode commutation speed			850	A/ μ s
T_{stg}	storage temperature			-55 to 150	$^\circ\text{C}$
T_j	junction temperature			-55 to 150	$^\circ\text{C}$

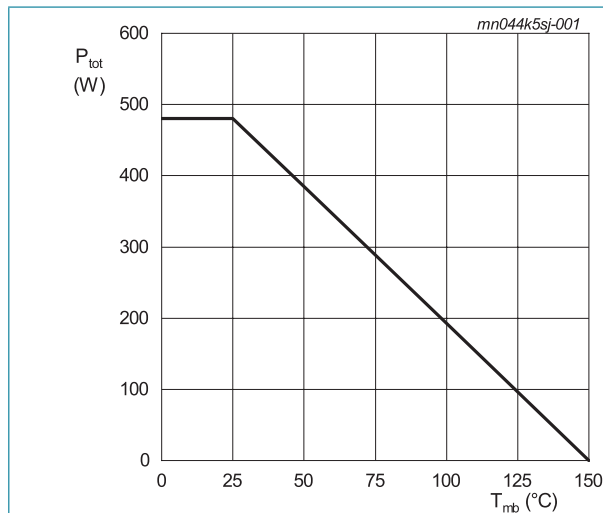


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

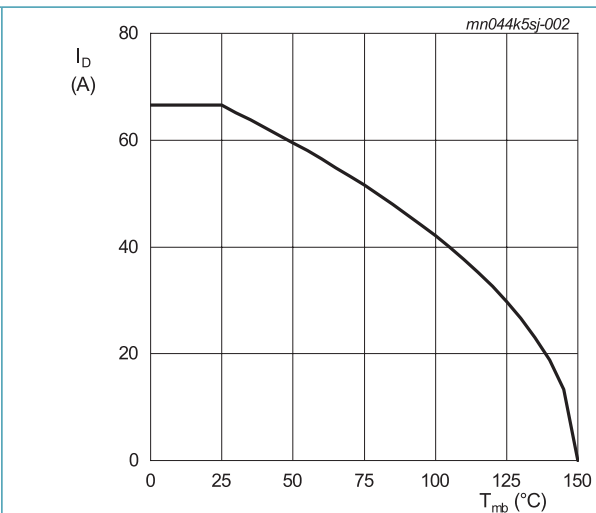


Fig. 2. Continuous Drain Current as a function of mounting base temperature

9. Thermal & Mechanical characteristics

Table 6. Thermal & Mechanical characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base			-	0.2	0.26	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	45	-	K/W

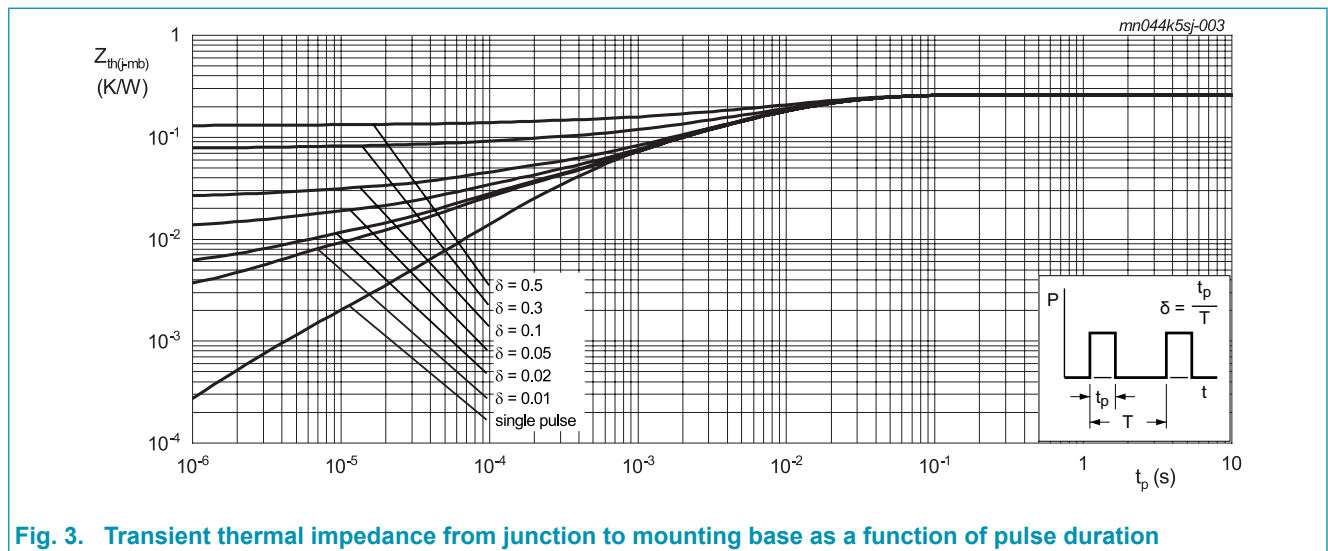


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics
 $T_j = 25\text{ °C}$ unless otherwise noted

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 1\text{ mA}; V_{GS} = 0\text{ V}$		650	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 250\text{ }\mu\text{A}; V_{DS} = V_{GS}$		3	-	5	V
I_{DSS}	drain leakage current	$V_{DS} = 650\text{ V}; V_{GS} = 0\text{ V}$		-	-	10	μA
		$V_{DS} = 650\text{ V}; V_{GS} = 0\text{ V}; T_j = 125\text{ °C}$		-	200	-	μA
I_{GSS}	gate leakage current	$V_{GS} = \pm 30\text{ V}; V_{DS} = 0\text{ V}$		-	-	± 500	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 34\text{ A}$		-	36	44	m Ω
R_G	gate resistance	$f = 1\text{ MHz}$		-	32	-	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	$I_D = 34\text{ A}; V_{DS} = 400\text{ V}; V_{GS} = 10\text{ V}$		-	123	-	nC
Q_{GS}	gate-source charge			-	40	-	nC
Q_{GD}	gate-drain charge			-	50	-	nC
C_{iss}	input capacitance	$V_{DS} = 400\text{ V}; V_{GS} = 0\text{ V}; f = 250\text{ kHz}$		-	6148	-	pF
C_{oss}	output capacitance			-	91	-	pF
C_{rss}	reverse transfer capacitance			-	0.6	-	pF
$C_{o(er)}$	effective output capacitance, energy related	$V_{GS} = 0\text{ V}; V_{DS} = 0\text{ to }400\text{ V}$		-	181	-	pF
$C_{o(tr)}$	effective output capacitance, time related			-	1598	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 400\text{ V}; V_{GS} = 10\text{ V}; R_G = 2\text{ }\Omega;$ $I_D = 34\text{ A}$		-	295	-	ns
t_r	rise time			-	25	-	ns
$t_{d(off)}$	turn-off delay time			-	433	-	ns
t_f	fall time			-	10	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	$V_{GS} = 0\text{ V}; I_S = 34\text{ A}$		-	0.94	1.2	V
I_S	body-diode continuous current	$T_{mb} = 25\text{ °C}$		-	-	67	A
t_{rr}	reverse recovery time	$V_R = 400\text{ V}; I_F = 34\text{ A}; di_F/dt = 100\text{ A}/\mu\text{s}$		-	184	-	ns
Q_{rr}	reverse recovered charge			-	1.6	-	μC
I_{rrm}	reverse recovery current			-	18	-	A

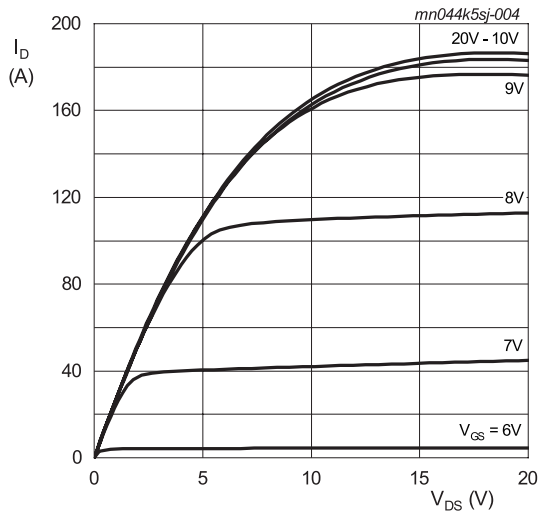


Fig. 4. Drain current as a function of drain-source voltage; typical values

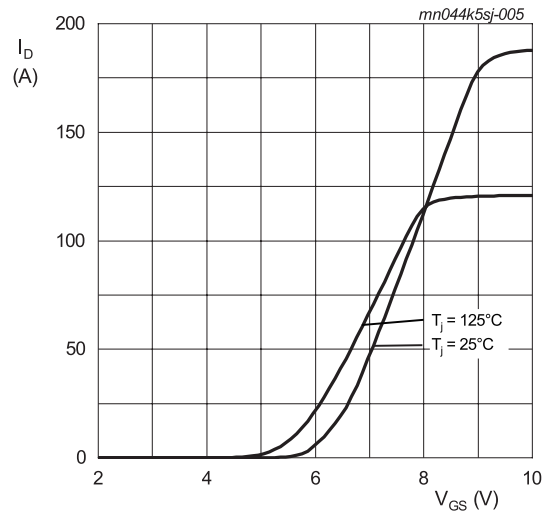


Fig. 5. Drain current as a function of gate-source voltage; typical values

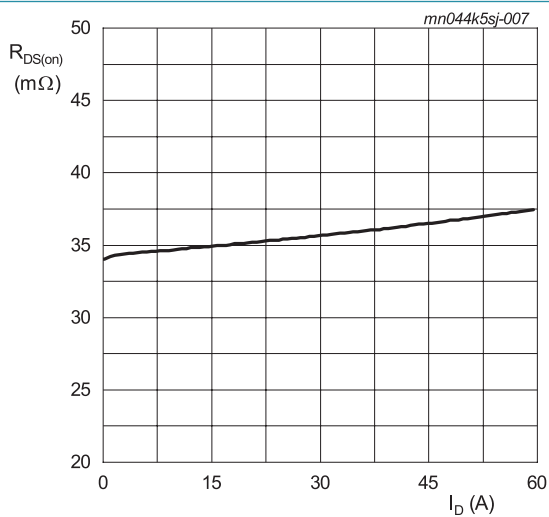


Fig. 6. Drain-source on-state resistance as a function of drain current; typical values

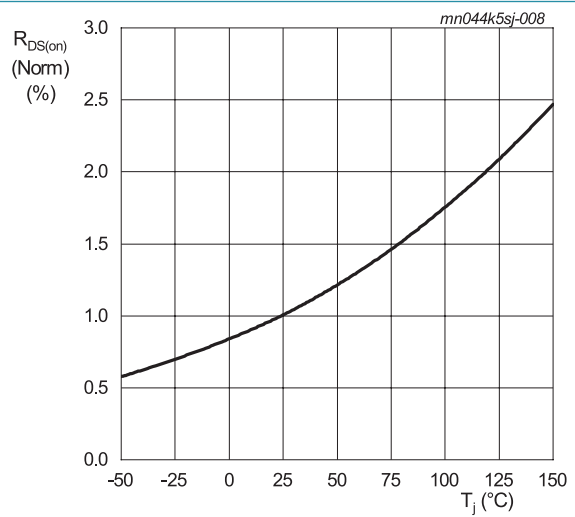
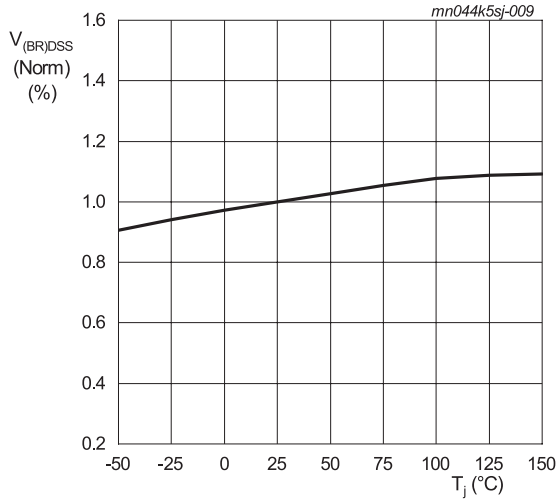
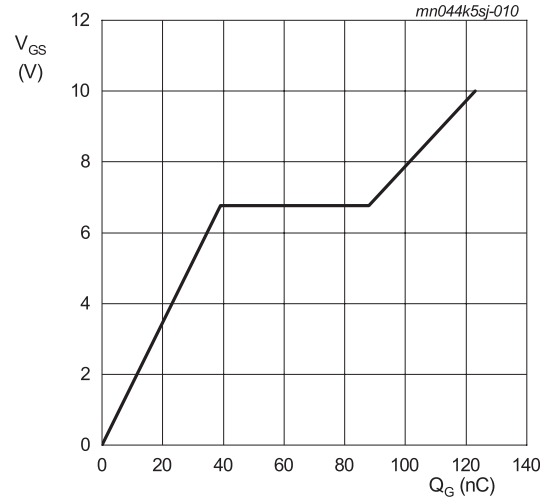


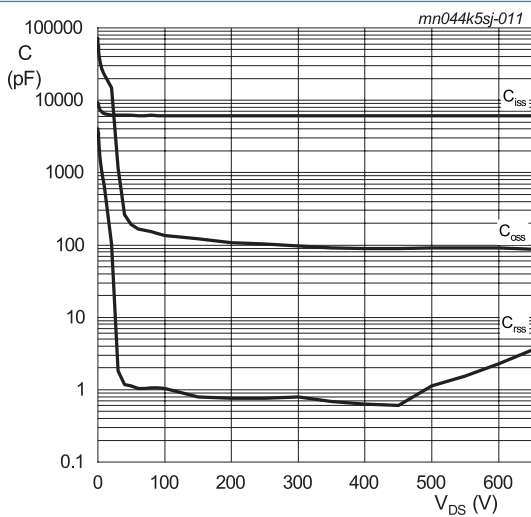
Fig. 7. Normalized drain-source on-state resistance as a function of junction temperature



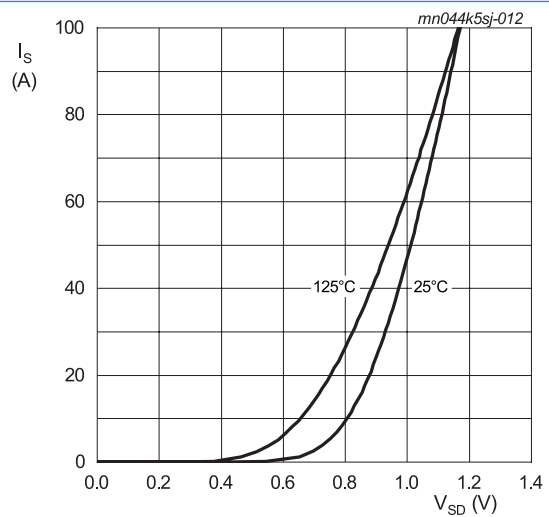
$I_D = 1 \text{ mA}$
Fig. 8. Normalized drain-source breakdown voltage as a function of junction temperature



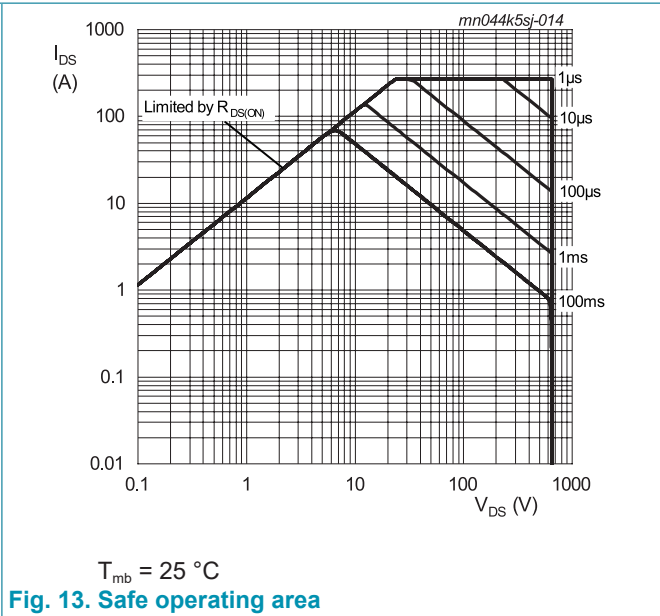
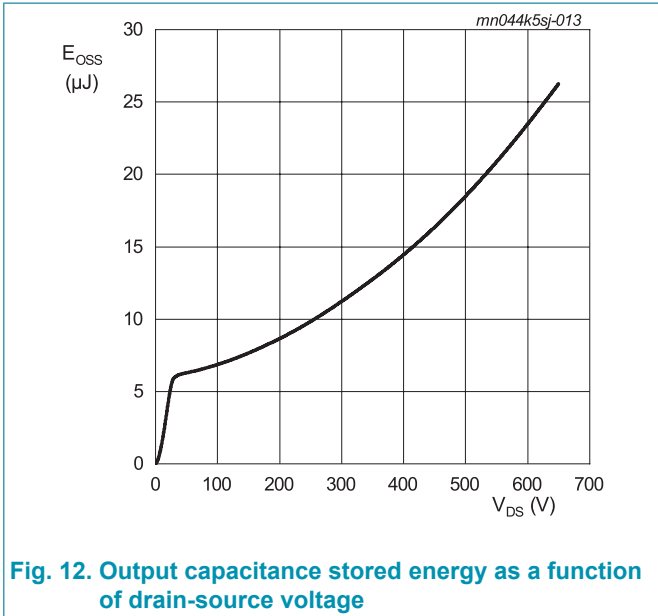
$I_D = 34 \text{ A}; V_{DS} = 400 \text{ V}$
Fig. 9. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0 \text{ V}; f = 250 \text{ kHz}$
Fig 10. Capacitances as a function of drain-source voltage; typical values



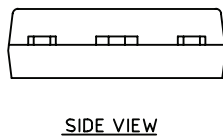
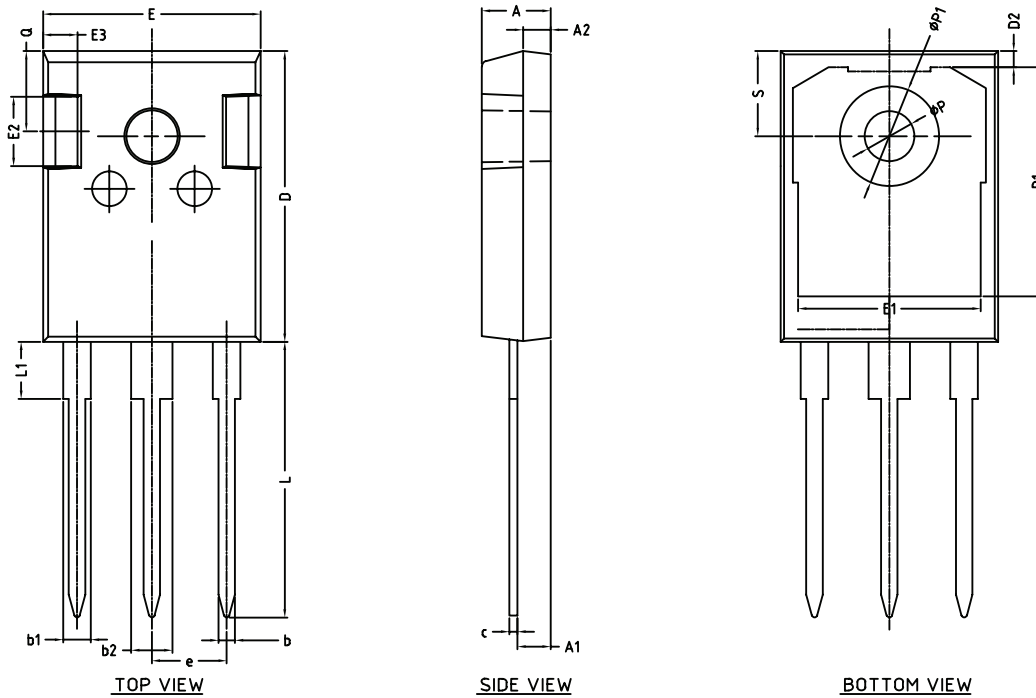
$V_{GS} = 0 \text{ V}$
Fig 11. Source current as a function of source-drain voltage; typical values



11. Package outline

Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247

SOT429N



UNIT	A	A1	A2	b	b1	b2	c	D	D1	D2	E	E1	E2	E3	e	L	L1	P	P1	Q	S	
mm	MAX	5.20	2.60	2.10	1.40	2.20	3.20	0.70	21.10	16.85	1.35	15.90	13.50	5.20	2.60	5.45	20.10	4.75	3.70	7.40	6.00	6.25
	MIN	4.70	2.20	1.90	1.00	1.80	2.80	0.50	20.90	16.25	1.05	15.70	13.10	4.80	2.40	19.80	-	3.50	-	5.60	6.05	

OUTLINE VERSION	REFERENCES				PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT429N		TO-247				

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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